

74AUP2G126

Low-power dual buffer/line driver; 3-state

Rev. 9 — 11 February 2013

Product data sheet

1. General description

The 74AUP2G126 provides the dual non-inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input (nOE). A LOW level at pin nOE causes the output to assume a high-impedance OFF-state. This device has the input-disable feature, which allows floating input signals. The inputs are disabled when the output enable input nOE is LOW.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V. This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - ◆ JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - ◆ JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - ◆ HBM JESD22-A114F Class 3A exceeds 5000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot $< 10\%$ of V_{CC}
- Input-disable feature allows floating input conditions
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$



3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AUP2G126DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74AUP2G126GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm	SOT833-1
74AUP2G126GF	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 × 1 × 0.5 mm	SOT1089
74AUP2G126GD	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 3 × 2 × 0.5 mm	SOT996-2
74AUP2G126GM	–40 °C to +125 °C	XQFN8	plastic, extremely thin quad flat package; no leads; 8 terminals; body 1.6 × 1.6 × 0.5 mm	SOT902-2
74AUP2G126GN	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.2 × 1.0 × 0.35 mm	SOT1116
74AUP2G126GS	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 × 1.0 × 0.35 mm	SOT1203

4. Marking

Table 2. Marking codes

Type number	Marking code ^[1]
74AUP2G126DC	p26
74AUP2G126GT	p26
74AUP2G126GF	pN
74AUP2G126GD	p26
74AUP2G126GM	p26
74AUP2G126GN	pN
74AUP2G126GS	pN

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

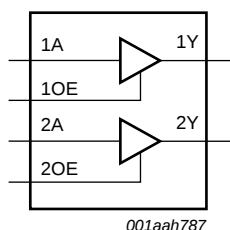


Fig 1. Logic symbol

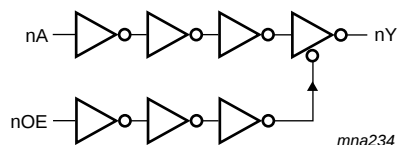
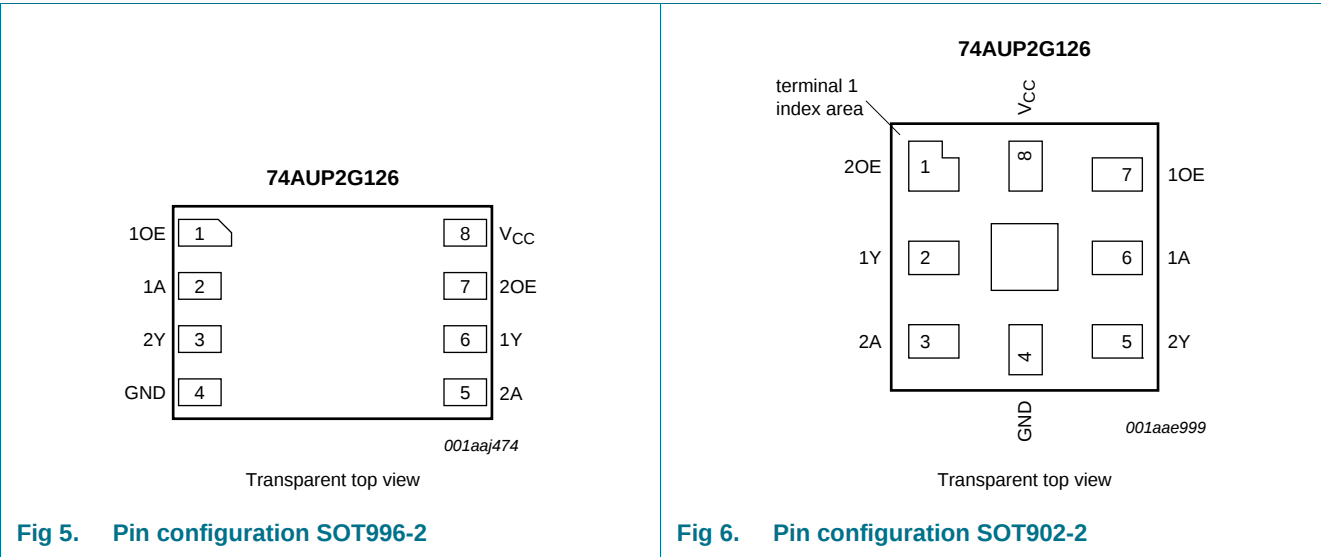
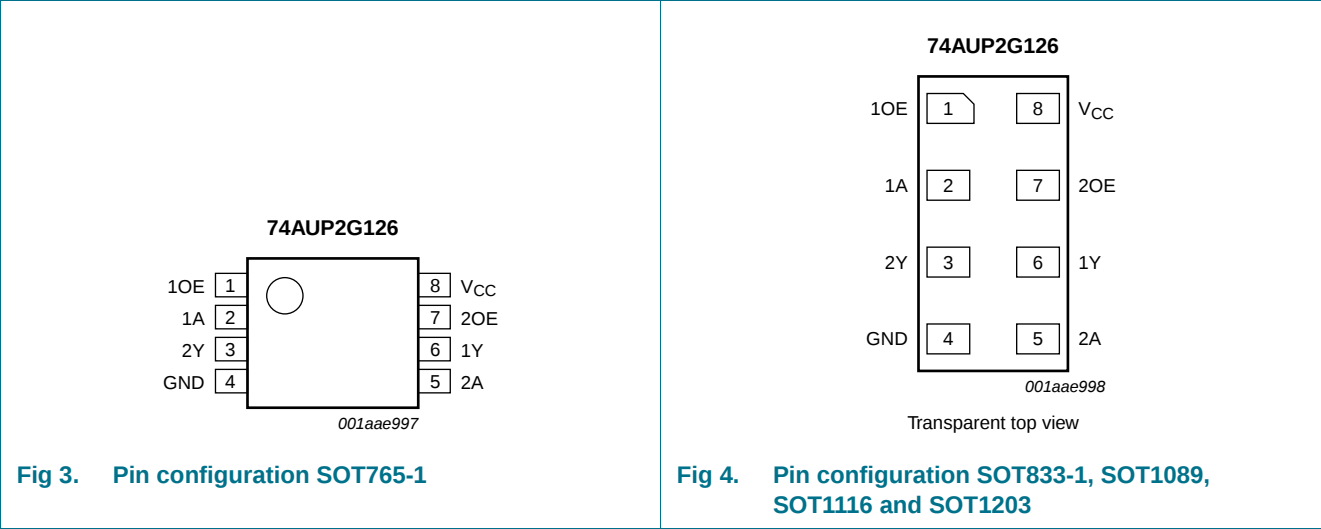


Fig 2. Logic diagram (one gate)

6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203	SOT902-2	
1OE, 2OE	1, 7	7, 1	output enable input (active HIGH)
1A, 2A	2, 5	6, 3	data input
1Y, 2Y	6, 3	2, 5	data output
GND	4	4	ground (0 V)
VCC	8	8	supply voltage

7. Functional description

Table 4. Function table^[1]

Input		Output
nOE	nA	nY
H	L	L
H	H	H
L	X	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
I_{IK}	input clamping current	$V_I < 0$ V	-50	-	mA
V_I	input voltage		^[1] -0.5	+4.6	V
I_{OK}	output clamping current	$V_O < 0$ V	-50	-	mA
V_O	output voltage	Active mode and Power-down mode	^[1] -0.5	+4.6	V
I_O	output current	$V_O = 0$ V to V_{CC}	-	±20	mA
I_{CC}	supply current		-	50	mA
I_{GND}	ground current		-50	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C	^[2] -	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For VSSOP8 packages: above 110 °C the value of P_{tot} derates linearly with 8.0 mW/K.
For XSON8 and XQFN8 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		0.8	3.6	V
V_I	input voltage		0	3.6	V
V_O	output voltage	Active mode	0	V_{CC}	V
		Power-down mode; $V_{CC} = 0$ V	0	3.6	V
T_{amb}	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 0.8$ V to 3.6 V	0	200	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 µA; V _{CC} = 0.8 V to 3.6 V	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.75 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.11	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.32	-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	2.05	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.9	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.72	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.6	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 µA; V _{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.31	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.44	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.31	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.44	V
I _I	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.1	µA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = 0 V to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.1	µA
I _{OFF}	power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V	-	-	±0.2	µA
ΔI _{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.2	µA
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	0.5	µA

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
ΔI_{CC}	additional supply current	data input; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 3.3$ V	[1] -	-	40	μ A
		nOE input; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 3.3$ V	[1] -	-	110	μ A
		all inputs; $V_I = \text{GND to } 3.6$ V; nOE = GND; $V_{CC} = 0.8$ V to 3.6 V	[2] -	-	1	μ A
C_I	input capacitance	$V_I = \text{GND or } V_{CC}$; $V_{CC} = 0$ V to 3.6 V	-	0.9	-	pF
C_O	output capacitance	output enabled; $V_O = \text{GND}$; $V_{CC} = 0$ V	-	1.7	-	pF
		output disabled; $V_O = \text{GND or } V_{CC}$; $V_{CC} = 0$ V to 3.6 V	-	1.5	-	pF
$T_{\text{amb}} = -40$ °C to +85 °C						
V_{IH}	HIGH-level input voltage	$V_{CC} = 0.8$ V	$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9$ V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3$ V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0$ V to 3.6 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 0.8$ V	-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 0.9$ V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		$V_{CC} = 2.3$ V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0$ V to 3.6 V	-	-	0.9	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -20$ μ A; $V_{CC} = 0.8$ V to 3.6 V	$V_{CC} - 0.1$	-	-	V
		$I_O = -1.1$ mA; $V_{CC} = 1.1$ V	$0.7 \times V_{CC}$	-	-	V
		$I_O = -1.7$ mA; $V_{CC} = 1.4$ V	1.03	-	-	V
		$I_O = -1.9$ mA; $V_{CC} = 1.65$ V	1.30	-	-	V
		$I_O = -2.3$ mA; $V_{CC} = 2.3$ V	1.97	-	-	V
		$I_O = -3.1$ mA; $V_{CC} = 2.3$ V	1.85	-	-	V
		$I_O = -2.7$ mA; $V_{CC} = 3.0$ V	2.67	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20$ μ A; $V_{CC} = 0.8$ V to 3.6 V	-	-	0.1	V
		$I_O = 1.1$ mA; $V_{CC} = 1.1$ V	-	-	$0.3 \times V_{CC}$	V
		$I_O = 1.7$ mA; $V_{CC} = 1.4$ V	-	-	0.37	V
		$I_O = 1.9$ mA; $V_{CC} = 1.65$ V	-	-	0.35	V
		$I_O = 2.3$ mA; $V_{CC} = 2.3$ V	-	-	0.33	V
		$I_O = 3.1$ mA; $V_{CC} = 2.3$ V	-	-	0.45	V
		$I_O = 2.7$ mA; $V_{CC} = 3.0$ V	-	-	0.33	V
I_I	input leakage current	$V_I = \text{GND to } 3.6$ V; $V_{CC} = 0$ V to 3.6 V	-	-	± 0.5	μ A
		$V_I = V_{IH}$ or V_{IL} ; $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	± 0.5	μ A
		V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	± 0.5	μ A
		V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	± 0.5	μ A
		V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	± 0.5	μ A
		V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	± 0.5	μ A
		V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	± 0.5	μ A
		V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	± 0.5	μ A

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
ΔI_{OFF}	additional power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	± 0.6	μA
I_{CC}	supply current	$V_I = GND$ or V_{CC} ; $I_O = 0$ A; $V_{CC} = 0.8$ V to 3.6 V	-	-	0.9	μA
ΔI_{CC}	additional supply current	data input; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 3.3$ V	[1] -	-	50	μA
		nOE input; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 3.3$ V	[1] -	-	120	μA
		all inputs; $V_I = GND$ to 3.6 V; nOE = GND; $V_{CC} = 0.8$ V to 3.6 V	[2] -	-	1	μA
$T_{amb} = -40$ °C to $+125$ °C						
V_{IH}	HIGH-level input voltage	$V_{CC} = 0.8$ V	$0.75 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9$ V to 1.95 V	$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3$ V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0$ V to 3.6 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 0.8$ V	-	-	$0.25 \times V_{CC}$	V
		$V_{CC} = 0.9$ V to 1.95 V	-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 2.3$ V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0$ V to 3.6 V	-	-	0.9	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -20$ μA ; $V_{CC} = 0.8$ V to 3.6 V	$V_{CC} - 0.11$	-	-	V
		$I_O = -1.1$ mA; $V_{CC} = 1.1$ V	$0.6 \times V_{CC}$	-	-	V
		$I_O = -1.7$ mA; $V_{CC} = 1.4$ V	0.93	-	-	V
		$I_O = -1.9$ mA; $V_{CC} = 1.65$ V	1.17	-	-	V
		$I_O = -2.3$ mA; $V_{CC} = 2.3$ V	1.77	-	-	V
		$I_O = -3.1$ mA; $V_{CC} = 2.3$ V	1.67	-	-	V
		$I_O = -2.7$ mA; $V_{CC} = 3.0$ V	2.40	-	-	V
		$I_O = -4.0$ mA; $V_{CC} = 3.0$ V	2.30	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20$ μA ; $V_{CC} = 0.8$ V to 3.6 V	-	-	0.11	V
		$I_O = 1.1$ mA; $V_{CC} = 1.1$ V	-	-	$0.33 \times V_{CC}$	V
		$I_O = 1.7$ mA; $V_{CC} = 1.4$ V	-	-	0.41	V
		$I_O = 1.9$ mA; $V_{CC} = 1.65$ V	-	-	0.39	V
		$I_O = 2.3$ mA; $V_{CC} = 2.3$ V	-	-	0.36	V
		$I_O = 3.1$ mA; $V_{CC} = 2.3$ V	-	-	0.50	V
		$I_O = 2.7$ mA; $V_{CC} = 3.0$ V	-	-	0.36	V
		$I_O = 4.0$ mA; $V_{CC} = 3.0$ V	-	-	0.50	V
I_I	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	± 0.75	μA
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	± 0.75	μA
I_{OFF}	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	± 0.75	μA

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
ΔI_{OFF}	additional power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	± 0.75	μA
I_{CC}	supply current	$V_I = GND$ or V_{CC} ; $I_O = 0$ A; $V_{CC} = 0.8$ V to 3.6 V	-	-	1.4	μA
ΔI_{CC}	additional supply current	data input; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 3.3$ V	[1] -	-	75	μA
		nOE input; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 3.3$ V	[1] -	-	180	μA
		all inputs; $V_I = GND$ to 3.6 V; nOE = GND; $V_{CC} = 0.8$ V to 3.6 V	[2] -	-	1	μA

[1] One input at $V_{CC} - 0.6$ V, other input at V_{CC} or GND.[2] To show I_{CC} remains very low when the input-disable feature is enabled.

11. Dynamic characteristics

Table 8. Dynamic characteristicsVoltages are referenced to GND (ground = 0 V); for test circuit see [Figure 9](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ [1]	Max	Min	Max (85 °C)	Max (125 °C)	

 $C_L = 5$ pF

t_{pd}	propagation delay	nA to nY; see Figure 7 [2]							
		$V_{CC} = 0.8$ V	-	20.6	-	-	-	-	ns
		$V_{CC} = 1.1$ V to 1.3 V	2.8	5.5	10.5	2.5	11.7	12.9	ns
		$V_{CC} = 1.4$ V to 1.6 V	2.2	3.9	6.1	2.0	7.3	8.1	ns
		$V_{CC} = 1.65$ V to 1.95 V	1.9	3.2	4.1	1.7	6.1	6.7	ns
		$V_{CC} = 2.3$ V to 2.7 V	1.6	2.6	3.6	1.4	4.3	4.9	ns
		$V_{CC} = 3.0$ V to 3.6 V	1.4	2.4	3.1	1.2	3.9	4.4	ns
t_{en}	enable time	nOE to nY; see Figure 8 [3]							
		$V_{CC} = 0.8$ V	-	71.6	-	-	-	-	ns
		$V_{CC} = 1.1$ V to 1.3 V	2.8	6.2	12.4	2.6	13.6	13.6	ns
		$V_{CC} = 1.4$ V to 1.6 V	2.3	4.2	6.9	2.2	7.4	7.7	ns
		$V_{CC} = 1.65$ V to 1.95 V	1.9	3.3	5.3	1.7	5.9	6.2	ns
		$V_{CC} = 2.3$ V to 2.7 V	1.5	2.4	3.6	1.4	3.8	4.1	ns
		$V_{CC} = 3.0$ V to 3.6 V	1.3	2.0	2.9	1.2	3.2	3.4	ns
t_{dis}	disable time	nOE to nY; see Figure 8 [4]							
		$V_{CC} = 0.8$ V	-	10.3	-	-	-	-	ns
		$V_{CC} = 1.1$ V to 1.3 V	2.6	4.2	6.2	2.9	6.4	6.5	ns
		$V_{CC} = 1.4$ V to 1.6 V	2.1	3.2	4.4	2.2	4.6	4.7	ns
		$V_{CC} = 1.65$ V to 1.95 V	2.1	3.1	4.4	1.7	4.6	4.8	ns
		$V_{CC} = 2.3$ V to 2.7 V	1.7	2.4	3.2	1.4	3.4	3.6	ns
		$V_{CC} = 3.0$ V to 3.6 V	2.1	2.8	3.6	1.2	3.7	3.8	ns

Table 8. Dynamic characteristics ...continuedVoltages are referenced to GND (ground = 0 V); for test circuit see [Figure 9](#).

Symbol	Parameter	Conditions	25 °C			−40 °C to +125 °C			Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 10 pF									
t _{pd}	propagation delay	nA to nY; see Figure 7	[2]						
		V _{CC} = 0.8 V	-	24.0	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.2	6.4	12.3	3.0	13.8	15.2	ns
		V _{CC} = 1.4 V to 1.6 V	2.1	4.5	7.3	1.9	8.5	9.4	ns
		V _{CC} = 1.65 V to 1.95 V	1.9	3.8	5.5	1.7	6.8	7.6	ns
		V _{CC} = 2.3 V to 2.7 V	2.1	3.2	4.2	1.6	5.3	5.9	ns
		V _{CC} = 3.0 V to 3.6 V	1.8	3.0	3.8	1.6	4.6	5.2	ns
t _{en}	enable time	nOE to nY; see Figure 8	[3]						
		V _{CC} = 0.8 V	-	75.3	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.2	7.1	14.1	3.0	15.4	15.4	ns
		V _{CC} = 1.4 V to 1.6 V	2.2	4.8	8.0	2.1	8.3	8.6	ns
		V _{CC} = 1.65 V to 1.95 V	1.8	3.9	5.9	1.7	6.5	6.8	ns
		V _{CC} = 2.3 V to 2.7 V	1.5	2.9	4.2	1.4	4.5	4.8	ns
		V _{CC} = 3.0 V to 3.6 V	1.4	2.6	3.6	1.3	3.8	4.0	ns
t _{dis}	disable time	nOE to nY; see Figure 8	[4]						
		V _{CC} = 0.8 V	-	12.2	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.5	5.3	7.6	3.3	7.9	7.9	ns
		V _{CC} = 1.4 V to 1.6 V	2.2	4.1	5.6	2.1	5.7	5.9	ns
		V _{CC} = 1.65 V to 1.95 V	2.4	4.2	5.7	1.7	5.8	6.0	ns
		V _{CC} = 2.3 V to 2.7 V	1.9	3.2	4.1	1.4	4.3	4.5	ns
		V _{CC} = 3.0 V to 3.6 V	2.4	4.1	5.0	1.3	5.2	5.3	ns
C _L = 15 pF									
t _{pd}	propagation delay	nA to nY; see Figure 7	[2]						
		V _{CC} = 0.8 V	-	27.4	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.6	7.2	14.1	3.3	15.8	17.5	ns
		V _{CC} = 1.4 V to 1.6 V	3.0	5.1	8.1	2.5	9.8	10.9	ns
		V _{CC} = 1.65 V to 1.95 V	2.2	4.3	6.3	2.0	7.9	8.8	ns
		V _{CC} = 2.3 V to 2.7 V	2.0	3.7	4.9	1.8	6.0	6.7	ns
		V _{CC} = 3.0 V to 3.6 V	2.0	3.5	4.4	1.8	5.4	6.1	ns
t _{en}	enable time	nOE to nY; see Figure 8	[3]						
		V _{CC} = 0.8 V	-	79.2	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.6	7.8	15.8	3.3	17.1	17.1	ns
		V _{CC} = 1.4 V to 1.6 V	3.0	5.4	8.8	2.9	9.4	9.7	ns
		V _{CC} = 1.65 V to 1.95 V	2.1	4.3	6.7	2.0	7.3	7.7	ns
		V _{CC} = 2.3 V to 2.7 V	1.8	3.4	4.8	1.7	5.2	5.6	ns
		V _{CC} = 3.0 V to 3.6 V	1.6	3.1	4.1	1.5	4.5	4.7	ns

Table 8. Dynamic characteristics ...continuedVoltages are referenced to GND (ground = 0 V); for test circuit see [Figure 9](#).

Symbol	Parameter	Conditions	25 °C			−40 °C to +125 °C			Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Max (125 °C)	
t _{dis}	disable time	nOE to nY; see Figure 8 ^[4]							
		V _{CC} = 0.8 V	-	14.9	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	4.3	6.4	8.5	3.7	9.3	9.4	ns
		V _{CC} = 1.4 V to 1.6 V	3.0	5.0	6.6	2.5	6.9	7.0	ns
		V _{CC} = 1.65 V to 1.95 V	3.1	5.4	6.6	2.0	7.4	7.5	ns
		V _{CC} = 2.3 V to 2.7 V	2.4	4.0	5.0	1.7	5.1	5.5	ns
		V _{CC} = 3.0 V to 3.6 V	3.2	5.3	6.2	1.5	6.7	6.9	ns
C _L = 30 pF									
t _{pd}	propagation delay	nA to nY; see Figure 7 ^[2]							
		V _{CC} = 0.8 V	-	37.4	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	4.8	9.5	18.7	4.4	21.4	24.0	ns
		V _{CC} = 1.4 V to 1.6 V	4.0	6.7	10.8	3.0	13.0	14.5	ns
		V _{CC} = 1.65 V to 1.95 V	2.9	5.6	8.4	2.6	10.3	11.5	ns
		V _{CC} = 2.3 V to 2.7 V	2.7	4.8	6.3	2.5	7.8	8.7	ns
		V _{CC} = 3.0 V to 3.6 V	2.7	4.6	5.8	2.5	7.0	8.3	ns
t _{en}	enable time	nOE to nY; see Figure 8 ^[3]							
		V _{CC} = 0.8 V	-	90.6	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	4.7	10.0	20.4	4.3	22.0	22.0	ns
		V _{CC} = 1.4 V to 1.6 V	3.0	6.9	11.3	3.7	12.0	12.5	ns
		V _{CC} = 1.65 V to 1.95 V	2.6	5.6	8.6	3.2	9.5	10.1	ns
		V _{CC} = 2.3 V to 2.7 V	2.3	4.5	6.3	2.9	6.8	7.3	ns
		V _{CC} = 3.0 V to 3.6 V	2.2	4.2	5.8	2.7	6.4	6.7	ns
t _{dis}	disable time	nOE to nY; see Figure 8 ^[4]							
		V _{CC} = 0.8 V	-	51.6	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	6.0	9.8	13.6	4.7	14.3	14.4	ns
		V _{CC} = 1.4 V to 1.6 V	4.5	7.7	10.5	3.0	10.7	11.0	ns
		V _{CC} = 1.65 V to 1.95 V	5.2	8.8	11.4	2.6	11.5	11.6	ns
		V _{CC} = 2.3 V to 2.7 V	3.9	6.4	7.4	2.3	9.0	10.2	ns
		V _{CC} = 3.0 V to 3.6 V	5.5	9.0	10.7	2.2	10.8	12.0	ns

Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 9](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +125 °C			Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Max (125 °C)	

$C_L = 5 \text{ pF}$, 10 pF , 15 pF and 30 pF

C_{PD}	power dissipation capacitance	output enabled; $f_i = 1 \text{ MHz}$; $V_i = \text{GND to } V_{CC}$ ^[5]							
		$V_{CC} = 0.8 \text{ V}$	-	2.7	-	-	-	-	pF
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	-	2.8	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	-	2.9	-	-	-	-	pF
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	-	3.0	-	-	-	-	pF
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	3.6	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	4.2	-	-	-	-	pF

[1] All typical values are measured at nominal V_{CC} .

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] t_{en} is the same as t_{PZH} and t_{PZL} .

[4] t_{dis} is the same as t_{PHZ} and t_{PLZ} .

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

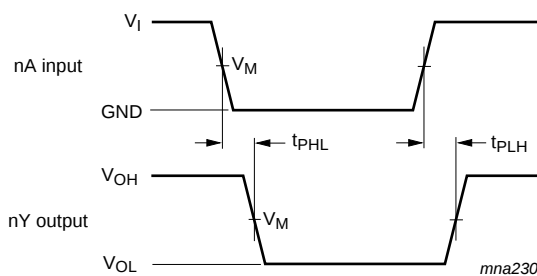
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms

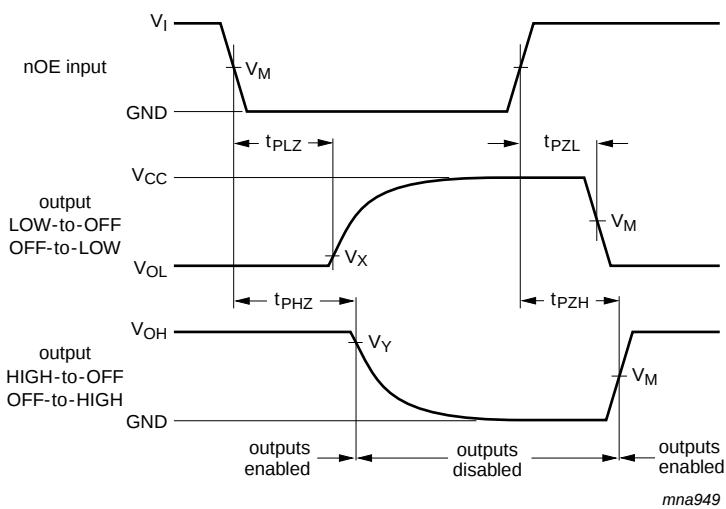


Measurement points are given in [Table 9](#).

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 7. The data input (nA) to output (nY) propagation delays**Table 9.** Measurement points

Supply voltage	Output	Input		
V_{CC}	V_M	V_M	V_i	$t_r = t_f$
0.8 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V_{CC}	$\leq 3.0 \text{ ns}$



Measurement points are given in [Table 10](#).
Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 8. Enable and disable times

Table 10. Measurement points

Supply voltage	Input	Output		
V_{CC}	V_M	V_M	V_x	V_y
0.8 V to 1.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{OL} + 0.1 \text{ V}$	$V_{OH} - 0.1 \text{ V}$
1.65 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{OL} + 0.15 \text{ V}$	$V_{OH} - 0.15 \text{ V}$
3.0 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{OL} + 0.3 \text{ V}$	$V_{OH} - 0.3 \text{ V}$

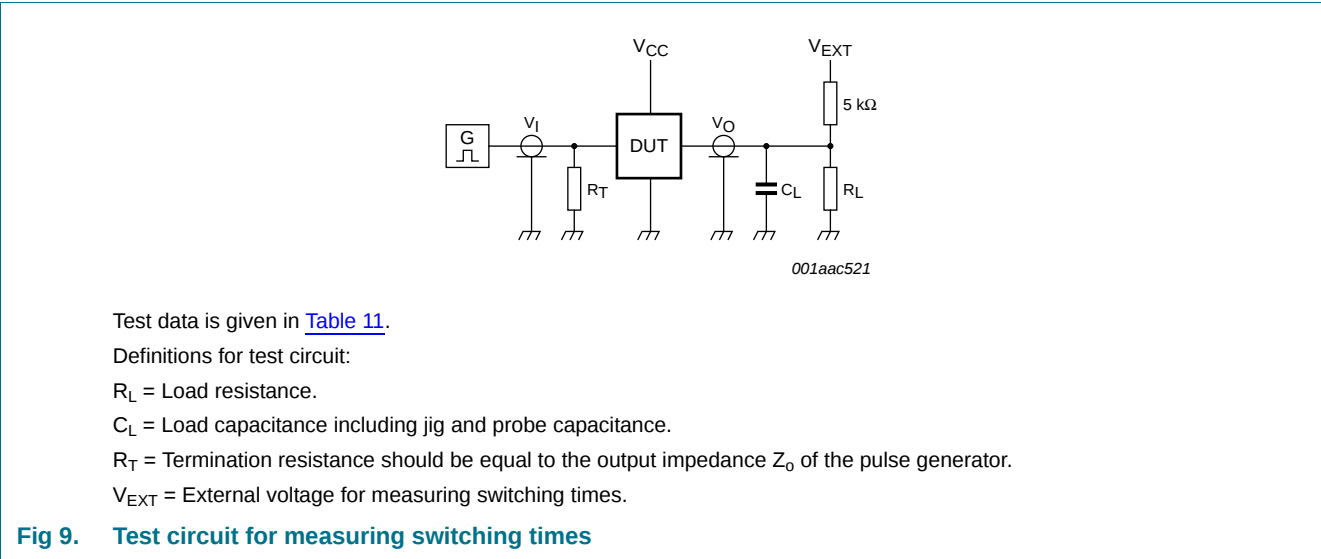


Table 11. Test data

Supply voltage	Load		V_{EXT}		
V_{CC}	C_L	R_L ^[1]	t_{PLH} , t_{PHL}	t_{PZH} , t_{PHZ}	t_{PZL} , t_{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times $R_L = 5\text{ k}\Omega$.
 For measuring propagation delays, set-up and hold times and pulse width $R_L = 1\text{ M}\Omega$.

13. Package outline

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

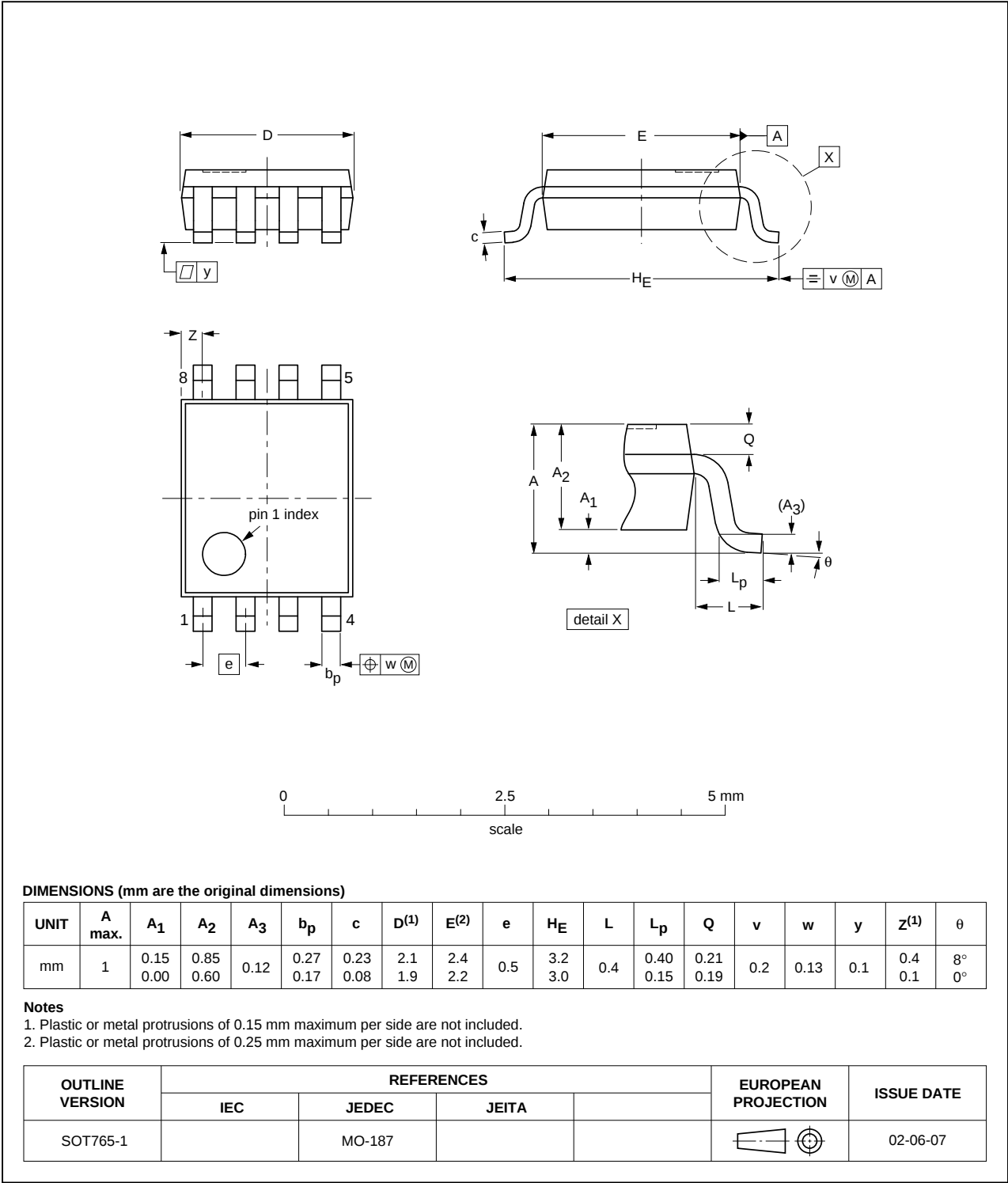


Fig 10. Package outline SOT765-1 (VSSOP8)

XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 1 x 1.95 x 0.5 mm

SOT833-1

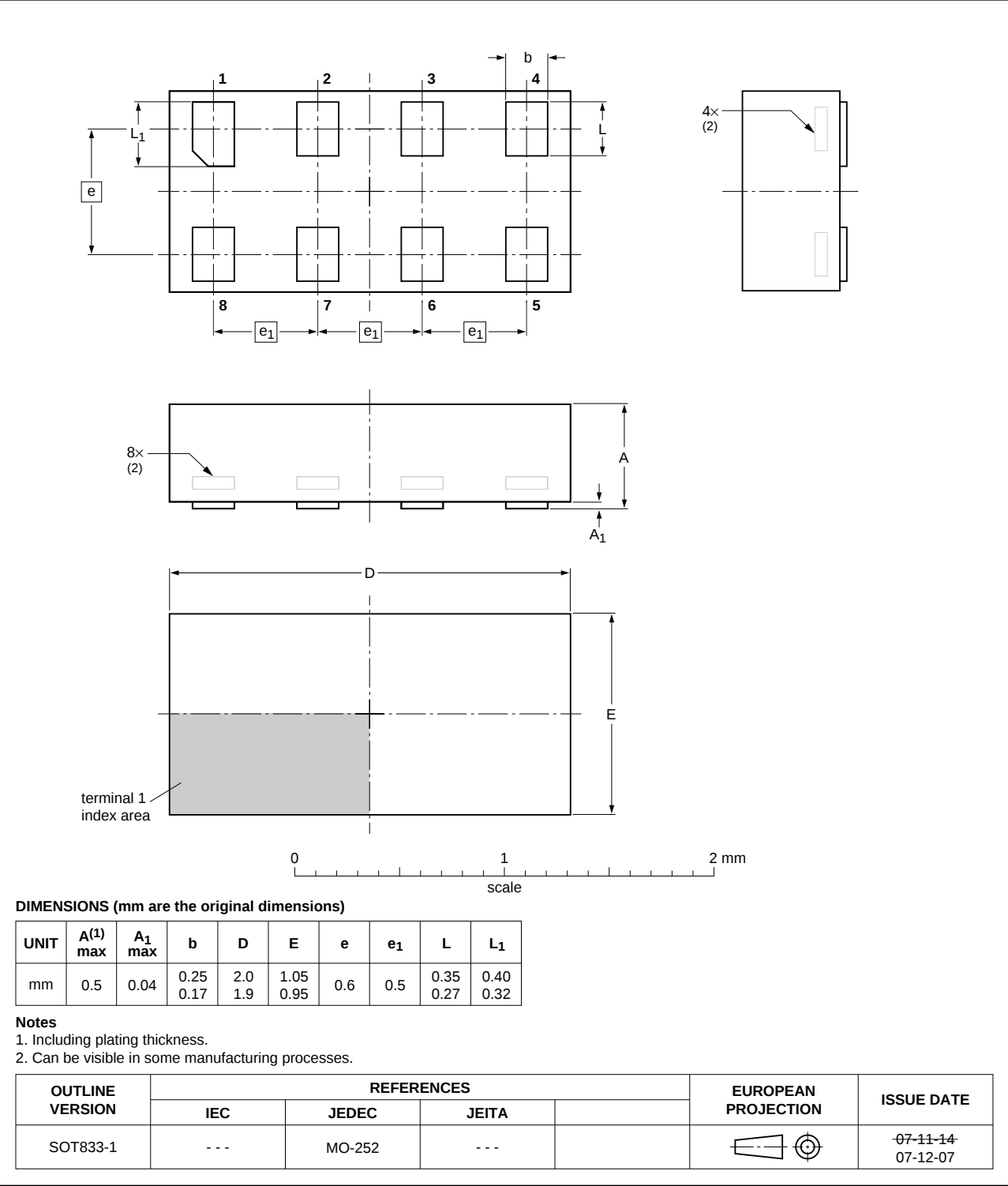


Fig 11. Package outline SOT833-1 (XSON8)

XSON8: extremely thin small outline package; no leads;
8 terminals; body 1.35 x 1 x 0.5 mm

SOT1089

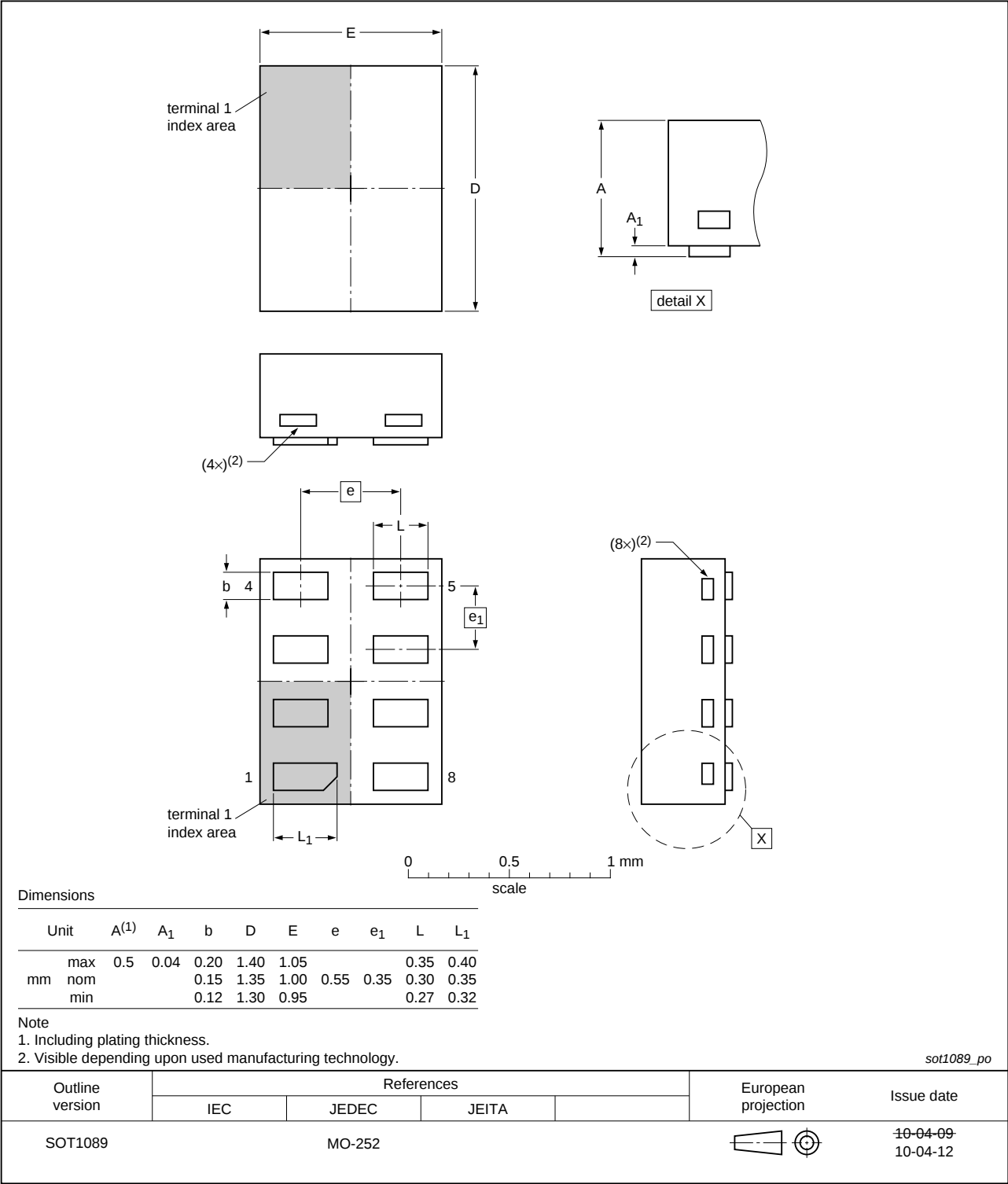


Fig 12. Package outline SOT1089 (XSON8)

XSON8: plastic extremely thin small outline package; no leads;
8 terminals; body 3 x 2 x 0.5 mm

SOT996-2

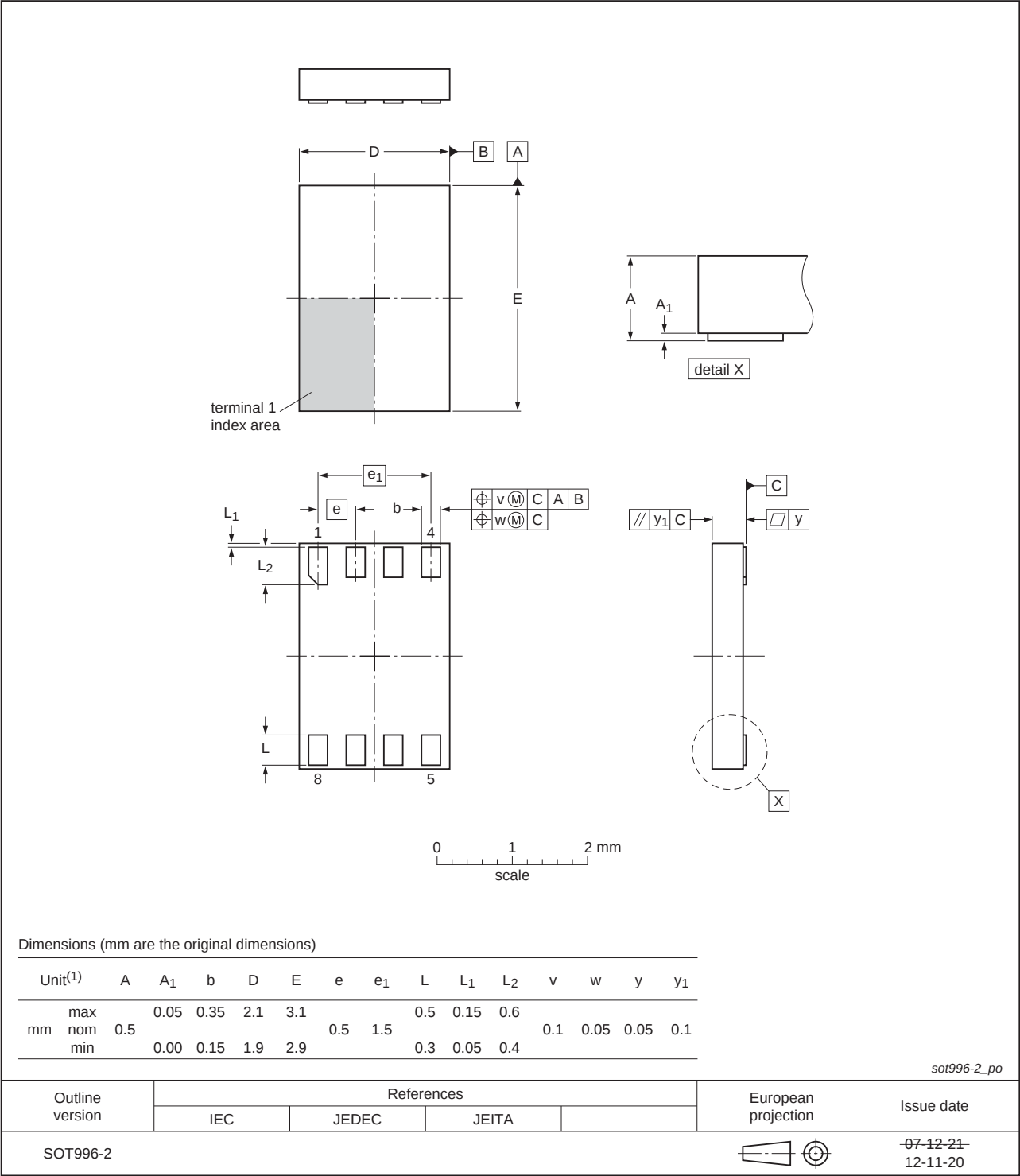


Fig 13. Package outline SOT996-2 (XSON8)

XQFN8: plastic, extremely thin quad flat package; no leads;
8 terminals; body 1.6 x 1.6 x 0.5 mm

SOT902-2

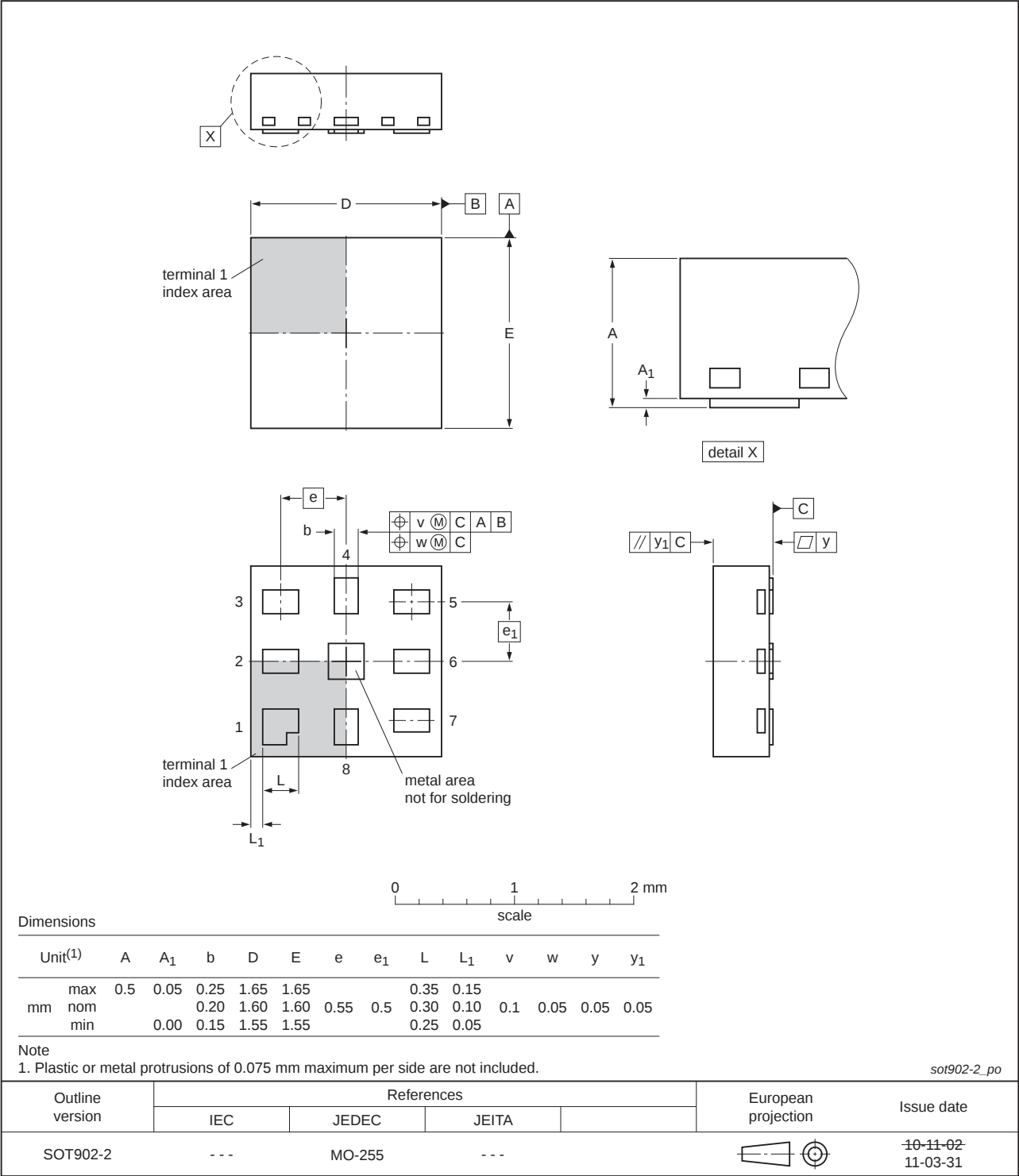
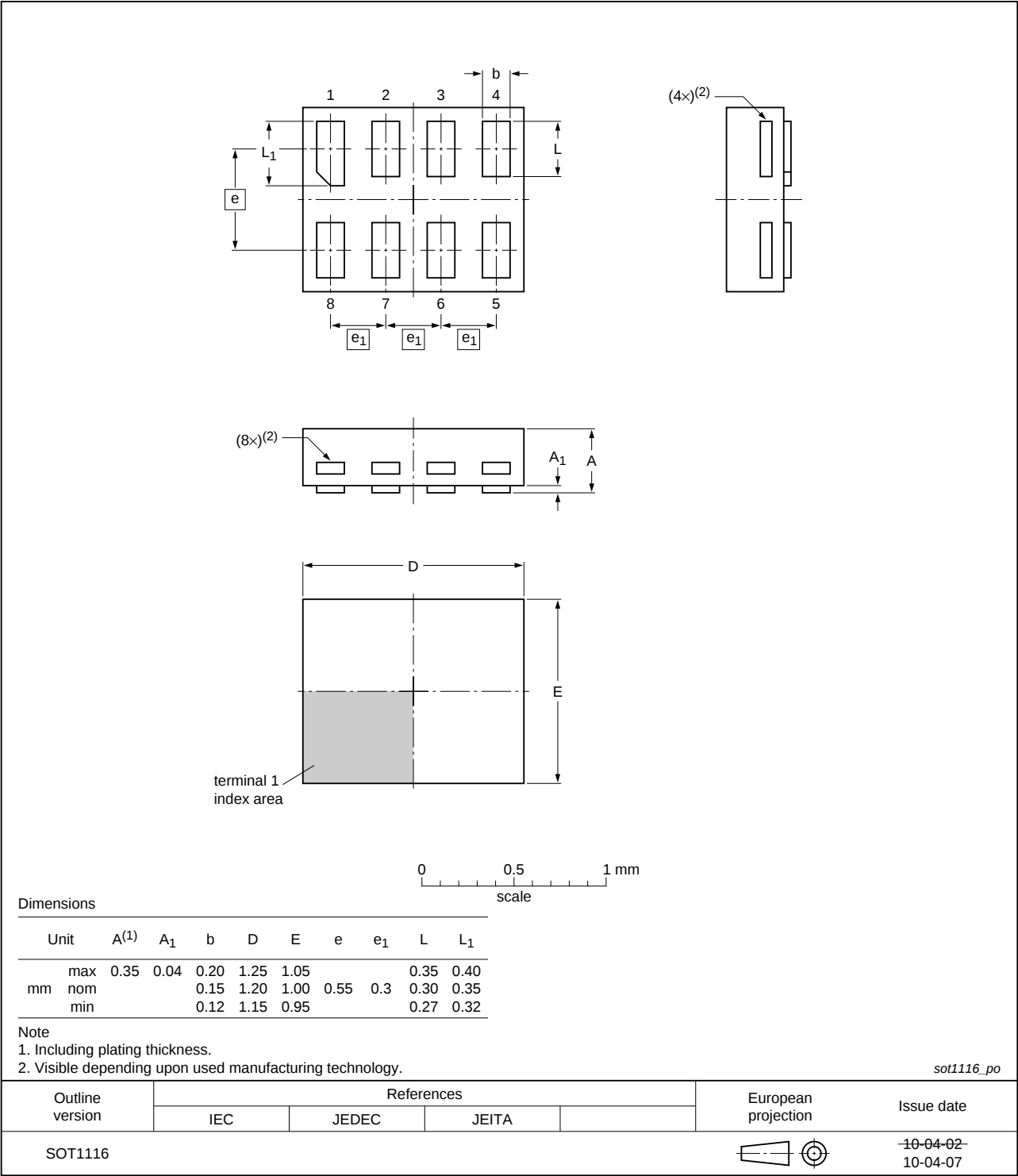


Fig 14. Package outline SOT902-2 (XQFN8)

XSON8: extremely thin small outline package; no leads;
8 terminals; body 1.2 x 1.0 x 0.35 mm

SOT1116



XSON8: extremely thin small outline package; no leads;
8 terminals; body 1.35 x 1.0 x 0.35 mm

SOT1203

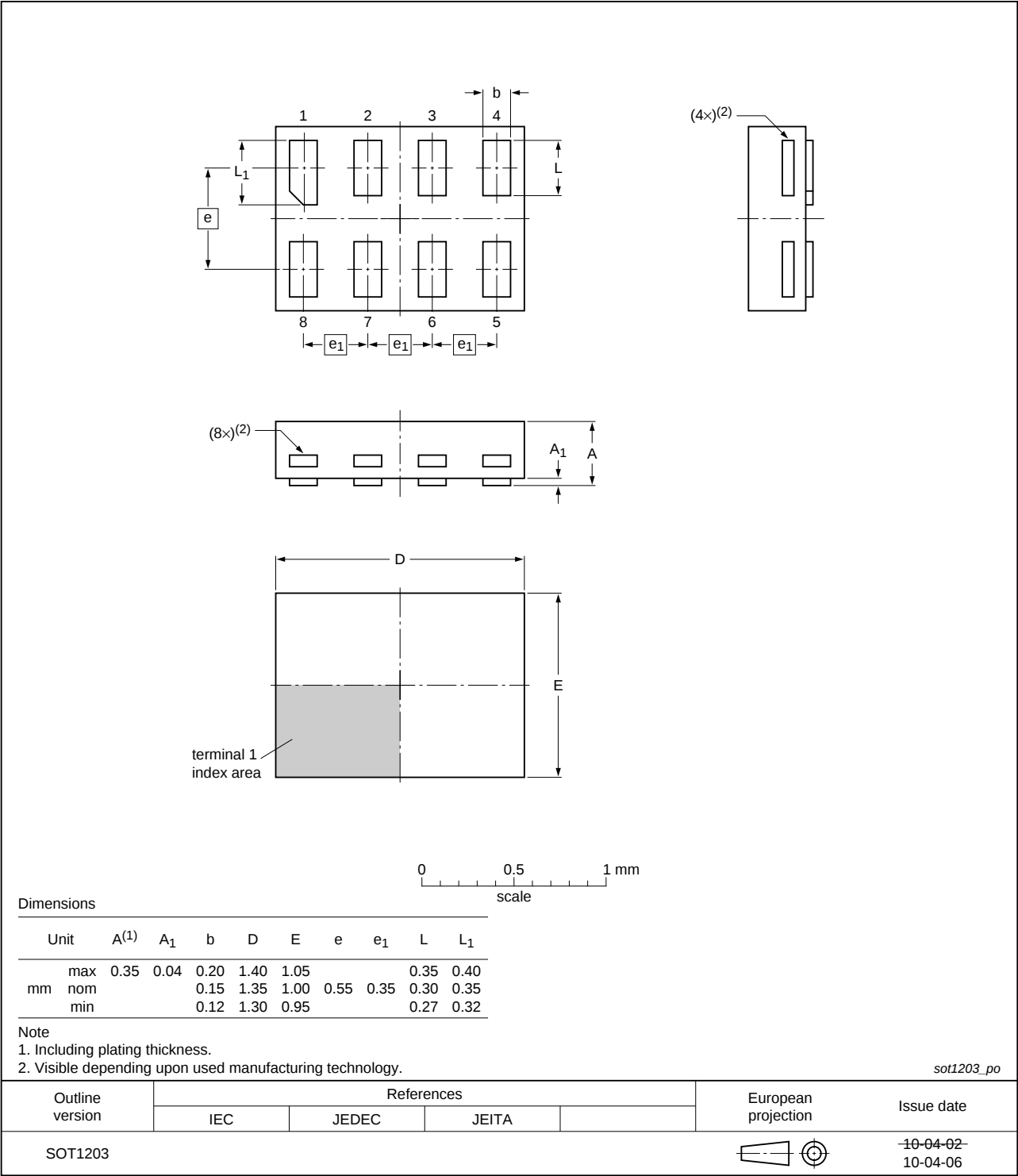


Fig 16. Package outline SOT1203 (XSON8)

14. Abbreviations

Table 12. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP2G126 v.9	20130211	Product data sheet	-	74AUP2G126 v.8
Modifications:	• For type number 74AUP2G126GD XSON8U has changed to XSON8.			
74AUP2G126 v.8	20120606	Product data sheet	-	74AUP2G126 v.7
74AUP2G126 v.7	20111201	Product data sheet	-	74AUP2G126 v.6
74AUP2G126 v.6	20100621	Product data sheet	-	74AUP2G126 v.5
74AUP2G126 v.5	20090202	Product data sheet	-	74AUP2G126 v.4
74AUP2G126 v.4	20090114	Product data sheet	-	74AUP2G126 v.3
74AUP2G126 v.3	20080409	Product data sheet	-	74AUP2G126 v.2
74AUP2G126 v.2	20070515	Product data sheet	-	74AUP2G126 v.1
74AUP2G126 v.1	20061009	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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18. Contents

1	General description	1
2	Features and benefits	1
3	Ordering information	2
4	Marking	2
5	Functional diagram	2
6	Pinning information	3
6.1	Pinning	3
6.2	Pin description	3
7	Functional description	4
8	Limiting values	4
9	Recommended operating conditions	4
10	Static characteristics	5
11	Dynamic characteristics	8
12	Waveforms	11
13	Package outline	14
14	Abbreviations	21
15	Revision history	21
16	Legal information	22
16.1	Data sheet status	22
16.2	Definitions	22
16.3	Disclaimers	22
16.4	Trademarks	23
17	Contact information	23
18	Contents	24

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Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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